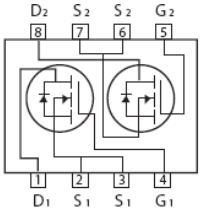
N-Channel Enhancement Mode MOSFET

Feature

- 16V, $R_{DS(ON)}$ = 26mΩ @V_{GS} = 4.5V , ID = 6.0A
  16V, $R_{DS(ON)}$ = 29mΩ @V_{GS} = 2.5V , ID = 5.2A
- Super High dense cell design for extremely low $R_{DS(ON)}$.
- Reliable and Rugged.
- TSSOP-8 for Surface Mount Package.

TSSOP-8



Applications:

- LI-ION Protection Circuit

Electrical Characteristics

T_A=25℃, Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
Off Characteristics						
Drain to Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250μA	16	-	-	V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=12V, V_{GS}=0V	-	-	1	μA
Gate Body Leakage Current, Forward	I_{GSSF}	V_{GS}=8V, V_{DS}=0V	-	-	100	nA
Gate Body Leakage Current, Reverse	I_{GSSR}	V_{GS}=-8V, V_{DS}=0V	-	-	-100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}= V_{DS}, I_D=250μA	0.4	-	1.3	V
Static Drain-source On-Resistance	$R_{DS(ON)}$	V_{GS} =4.5V, I_D =6.0A	-	26	28	mΩ
		V_{GS} =2.5V, I_D =5.2A	-	29	40	mΩ
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS} =0V, I_S=1.5A			1.2	V

Cross Reference

	SamHop			
STC5N20V	**SDG8204**			

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